Alfa-MOS Technology

AFN8822

20V Common-Drain N-Channel Enhancement Mode MOSFET

General Description

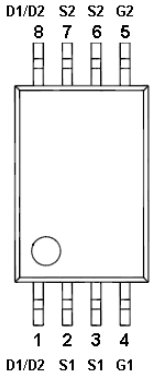
AFN8822, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

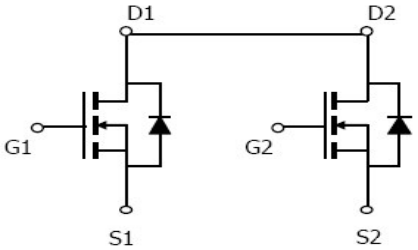
These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 20V/7.2A,$R_{DS(ON)}$=28mΩ@V_{GS}=4.5V
- 20V/4.8A,$R_{DS(ON)}$=32mΩ@V_{GS}=2.5V
- 20V/3.0A,$R_{DS(ON)}$=45mΩ@V_{GS}=1.8V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- TSSOP-8P package design

Pin Description (TSSOP-8P)





Application

- Load Switch
- Portable Equipment
- Battery Powered System

Pin Define

Pin	Symbol	Description
1	D1 / D2	Drain
2	S1	Source
3	S1	Source
4	G1	Gate
5	G2	Gate
6	S2	Source
7	S2	Source
8	D1 / D2	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN8822TS8RG	8822	TSSOP-8P	Tape & Reel	3000 EA

※ A Lot code
※ B Date code
※ AFN8822TS8RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

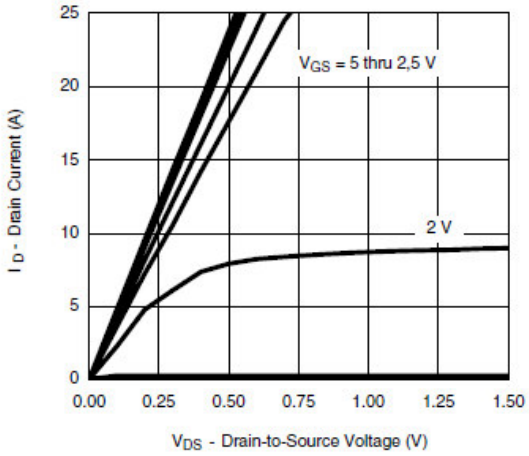
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	7.2	A
	T_A=70℃		4.8	
Pulsed Drain Current		I_{DM}	20	A
Continuous Source Current(Diode Conduction)		I_S	1.5	A
Power Dissipation	T_A=25℃	P_D	2.8	W
	T_A=70℃		1.8	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	62.5	℃/W

Electrical Characteristics

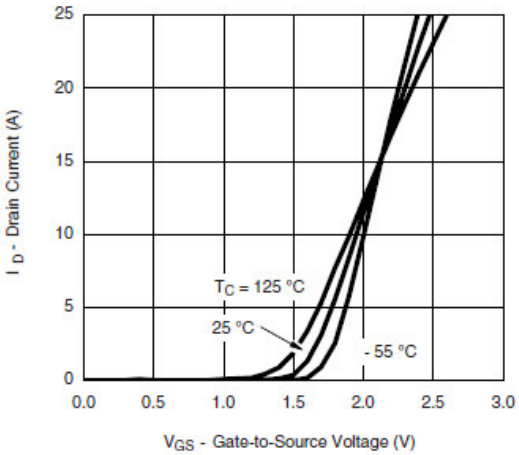
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	0.4		0.8	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V,V_{GS}=0V			1	uA
		V_{DS}=16V,V_{GS}=0V T_J=85℃			30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=4.5V	10			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}= 4.5V,I_D=7.2A		24	28	mΩ
		V_{GS}= 2.5V,I_D=4.8A		27	32	
		V_{GS}= 1.8V,I_D=3.0A		36	45	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=7A		25		S
Diode Forward Voltage	V_{SD}	I_S=1.6A,V_{GS}=0V		0.7	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=10V,V_{GS}=4.5V I_D≡7.0A		650		pC
Gate-Source Charge	Q_{gs}			200		
Gate-Drain Charge	Q_{gd}			180		
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1MHz		700		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			45		
Turn-On Time	$t_{d(on)}$	V_{DD}=10V,R_L=1.4Ω I_D≡1.0A,V_{GEN}=4.5V R_G=3Ω		8	12	ns
	t_r			12	20	
Turn-Off Time	$t_{d(off)}$			32	40	
	t_f			10	15	

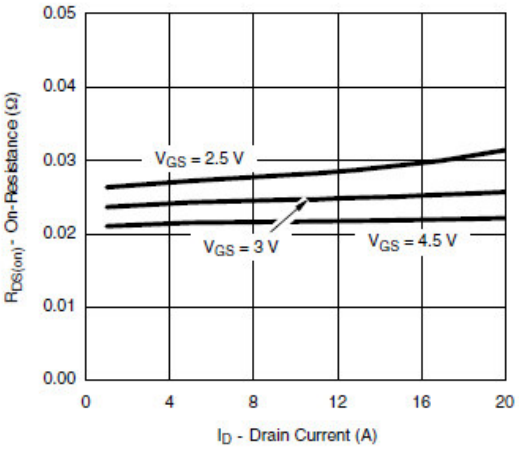
Typical Characteristics



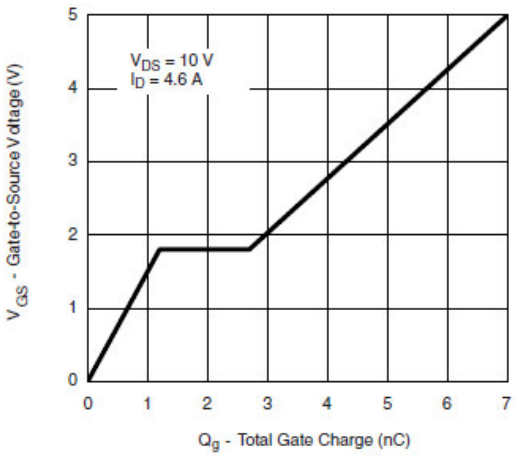
Output Characteristics



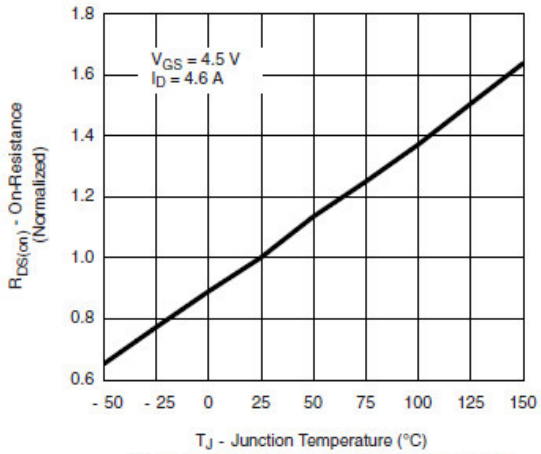
Transfer Characteristics



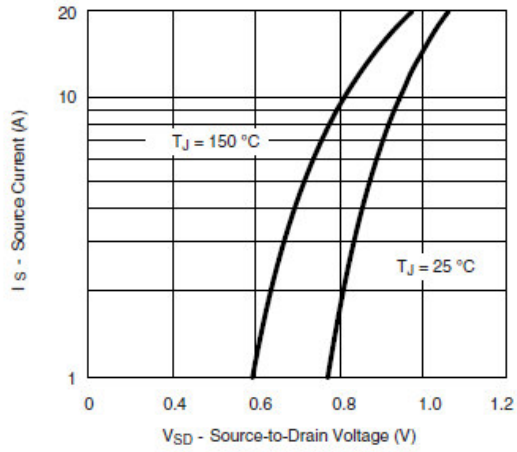
On-Resistance vs. Drain Current



Gate Charge

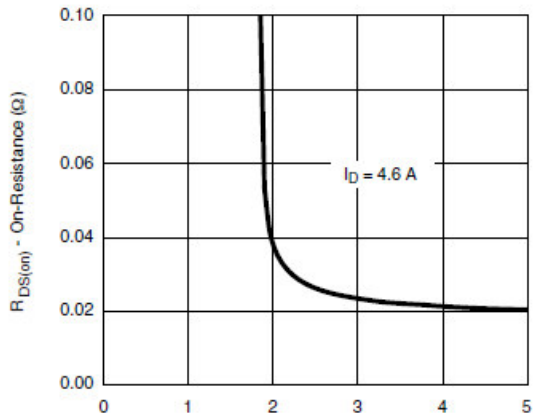


On-Resistance vs. Junction Temperature

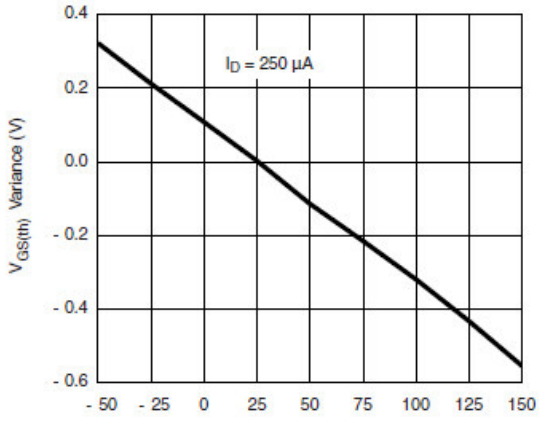


Source-Drain Diode Forward Voltage

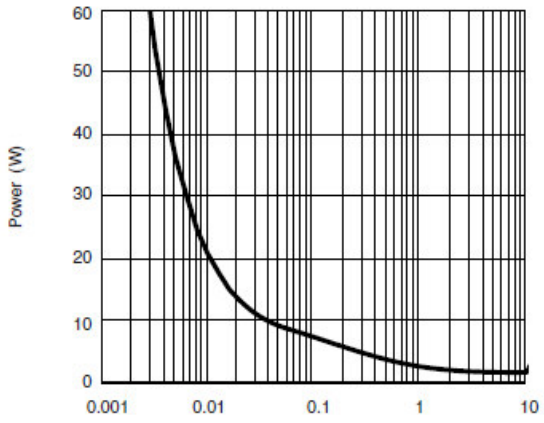
Typical Characteristics



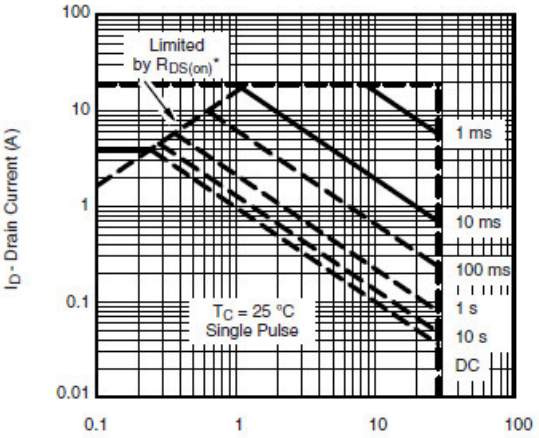
On-Resistance vs. Gate-to-Source Voltage



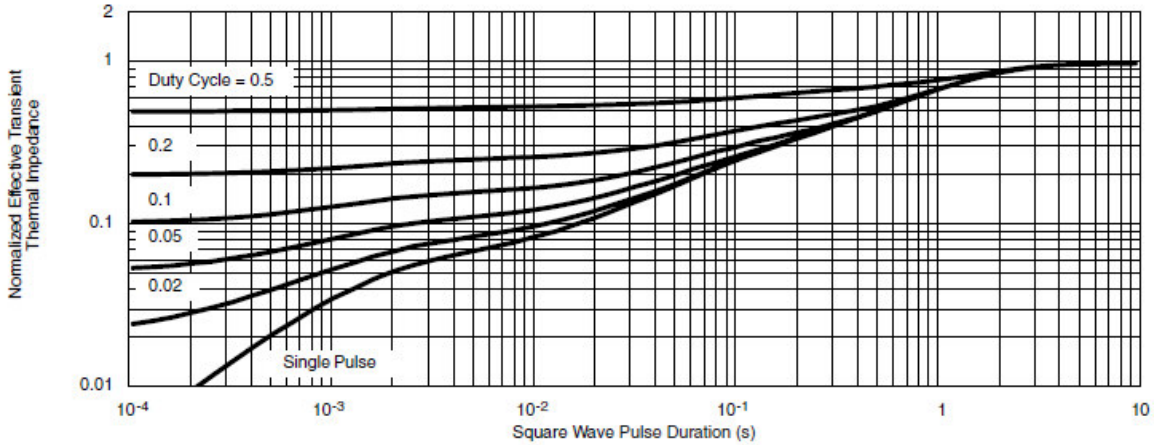
Threshold Voltage



Single Pulse Power



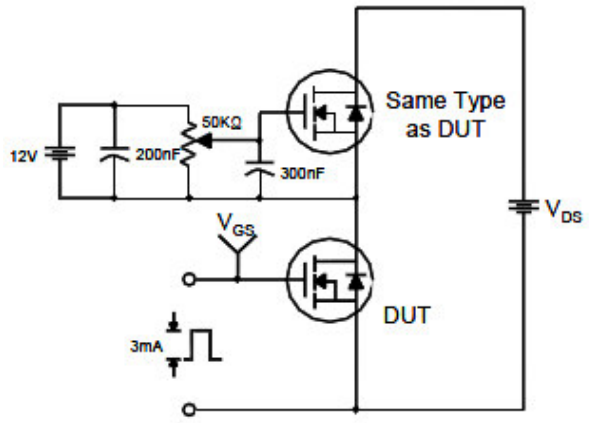
Safe Operating Area

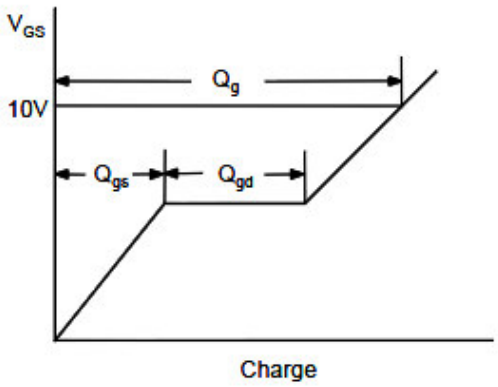


Normalized Thermal Transient Impedance, Junction-to-Foot

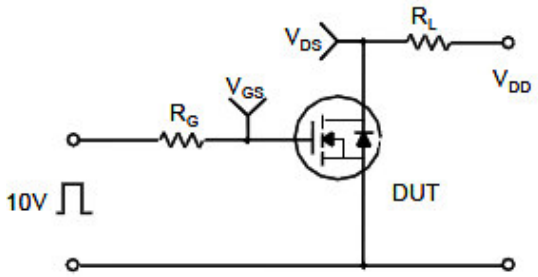
Typical Characteristics

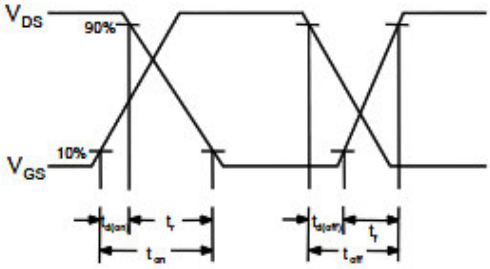
Gate Charge Test Circuit & Waveform



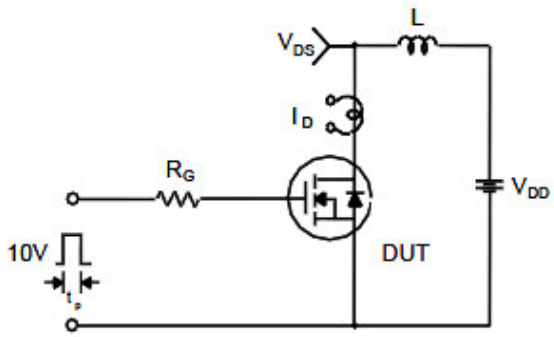


Resistive Switching Test Circuit & Waveforms

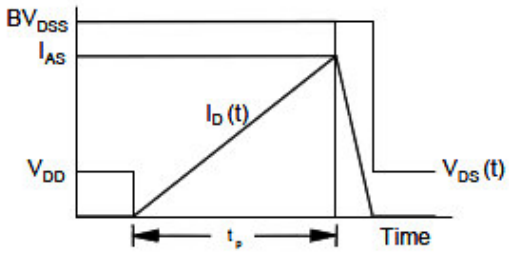




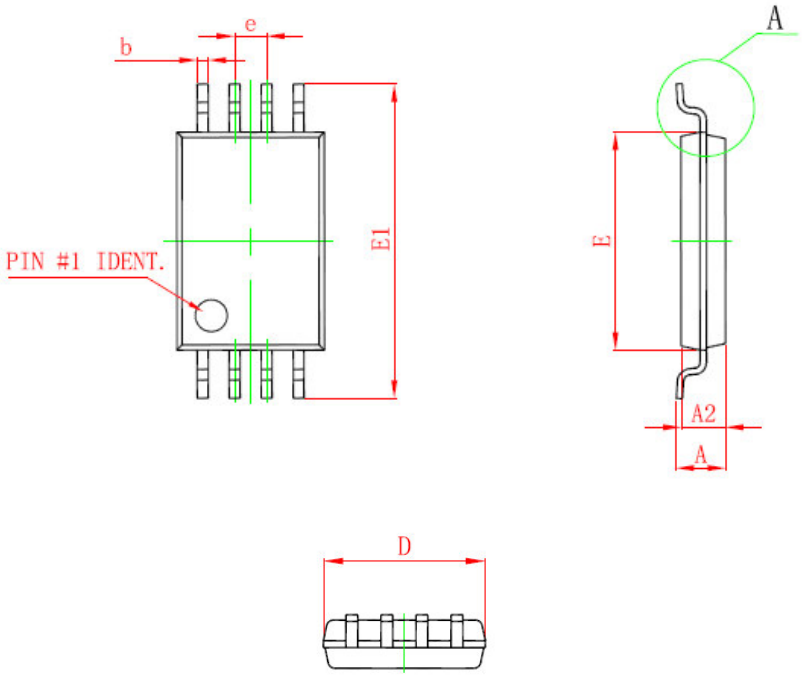
Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Package Information (TSSOP-8P)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.100		0.043
A2	0.800	1.000	0.031	0.039
A1	0.020	0.150	0.001	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25 (TYP)		0.01 (TYP)	
θ	1°	7°	1°	7°

©2010 Alfa-MOS Technology Co., Ltd.
2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)
Tel : 886 2) 2651 3928
Fax : 886 2) 2786 8483
©http://www.alfa-mos.com